

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

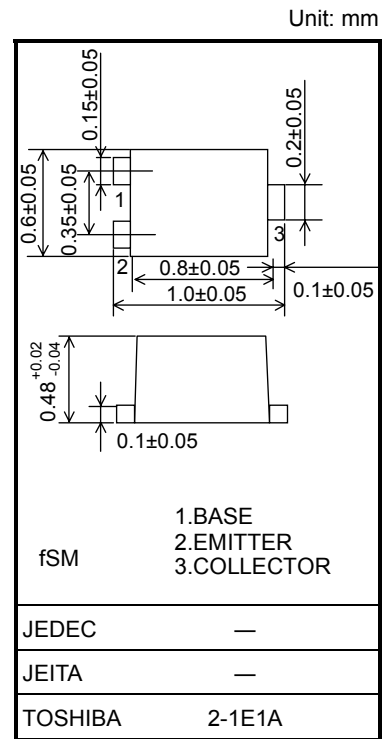
2SC6026

General-Purpose Amplifier Applications

- High voltage and high current
: $V_{CE0} = 50\text{ V}$, $I_C = 100\text{ mA}$ (max)
- Excellent h_{FE} linearity : $h_{FE}(I_C = 0.1\text{ mA})/h_{FE}(I_C = 2\text{ mA}) = 0.95$ (typ.)
- High h_{FE} : $h_{FE} = 120\sim 400$
- Complementary to 2SA2154
- Lead (Pb) free

Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Base current	I_B	30	mA
Collector power dissipation	P_C	50	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55~150	°C



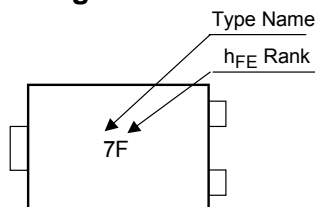
Weight: 0.0006 g (typ.)

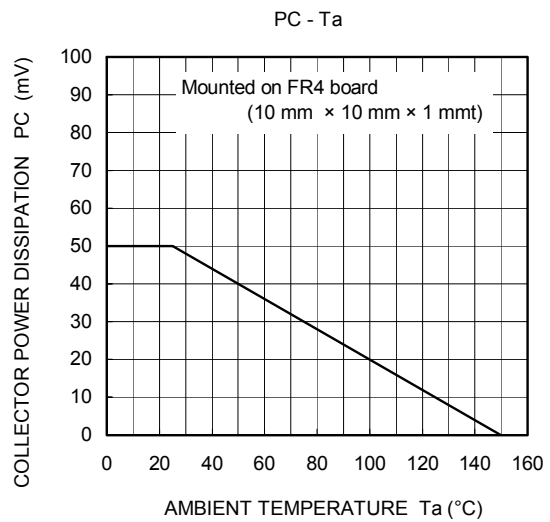
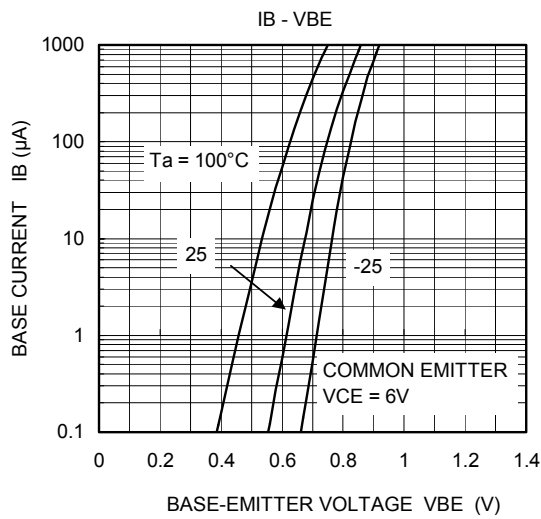
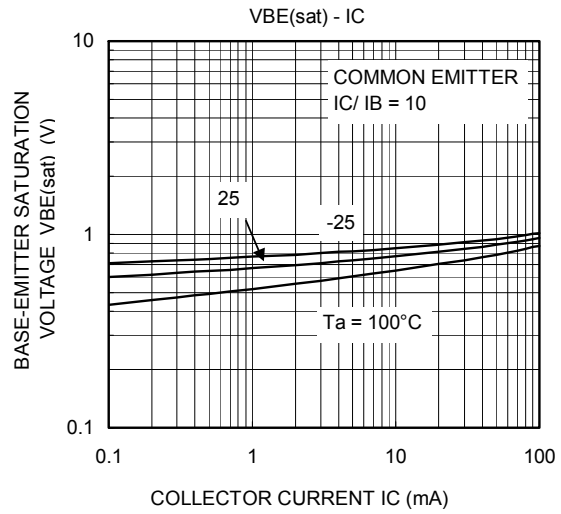
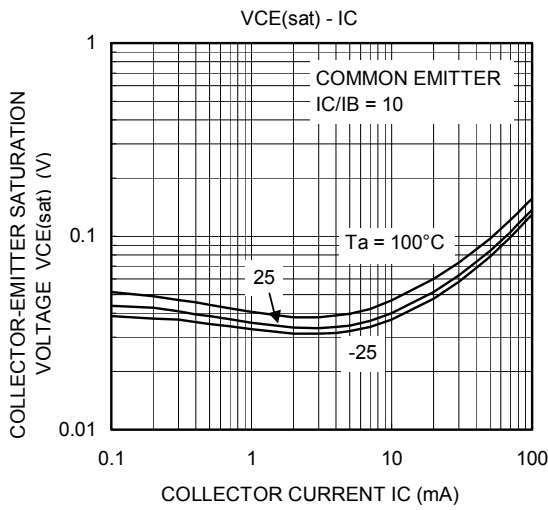
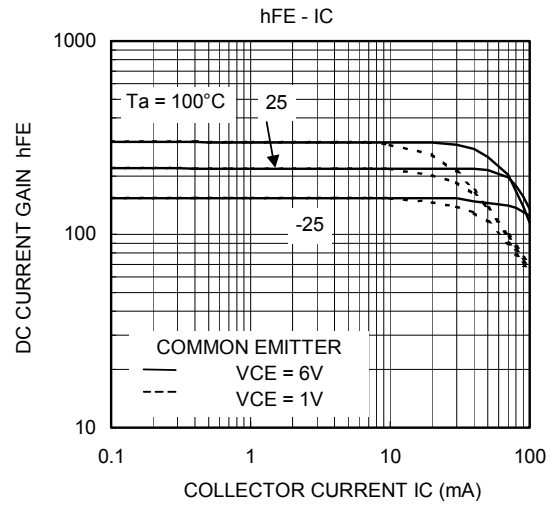
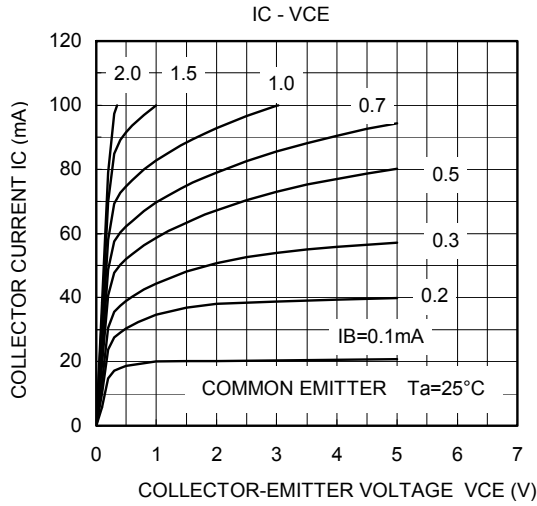
Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 60\text{ V}$, $I_E = 0$	—	—	0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 5\text{ V}$, $I_C = 0$	—	—	0.1	μA
DC current gain	h_{FE} (Note)	$V_{CE} = 6\text{ V}$, $I_C = 2\text{ mA}$	120	—	400	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100\text{ mA}$, $I_B = 10\text{ mA}$	—	0.1	0.25	V
Transition frequency	f_T	$V_{CE} = 10\text{ V}$, $I_C = 1\text{ mA}$	60	—	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$	—	0.95	—	pF

Note: h_{FE} classification Y (F): 120~240, GR (H): 200~400
() marking symbol

Marking





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